NSN 5962-01-420-7034

Memory Microcircuit - Page 1 of 1



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Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
End Application:
Pacer dawn
Features Provided:
Hermetically sealed and burn in and programmable and positive outputs and electrostatic sensitive
Inclosure Material:
Ceramic and glass
Inclosure Configuration:
Leadless flat pack
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
16 input
Criticality Code Justification:
Cbbl
Case Outline Source And Designator:
C-2 mil-m-38510
Terminal Surface Treatment:
Solder
Voltage Rating And Type Per Characteristic:
-0.5 volts power source and 7.0 volts power source
Time Rating Per Chacteristic:
30.00 nanoseconds propagation delay time, low to high level output and 30.00 nanoseconds propagation delay time, high to low level
output
Memory Device Type:
Pal
Test Data Document:
96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And Quantity:
20 leadless
Shelf Life:
N/a
Unit Of Measure:
Demilitarization:
No
Fiig:
A458a0